

MC74VHC573

Octal D-Type Latch with 3-State Output

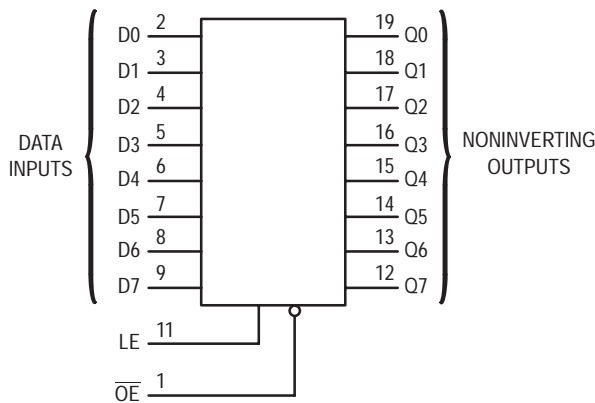
The MC74VHC573 is an advanced high speed CMOS octal latch with 3-state output fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

This 8-bit D-type latch is controlled by a latch enable input and an output enable input. When the output enable input is high, the eight outputs are in a high impedance state.

The internal circuit is composed of three stages, including a buffer output which provides high noise immunity and stable output. The inputs tolerate voltages up to 7V, allowing the interface of 5V systems to 3V systems.

- High Speed: $t_{PD} = 4.5\text{ns}$ (Typ) at $V_{CC} = 5\text{V}$
- Low Power Dissipation: $I_{CC} = 4\mu\text{A}$ (Max) at $T_A = 25^\circ\text{C}$
- High Noise Immunity: $V_{NIH} = V_{NIL} = 28\% V_{CC}$
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Designed for 2V to 5.5V Operating Range
- Low Noise: $V_{OLP} = 1.2\text{V}$ (Max)
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300mA
- ESD Performance: HBM > 2000V; Machine Model > 200V
- Chip Complexity: 218 FETs or 54.5 Equivalent Gates

LOGIC DIAGRAM



FUNCTION TABLE

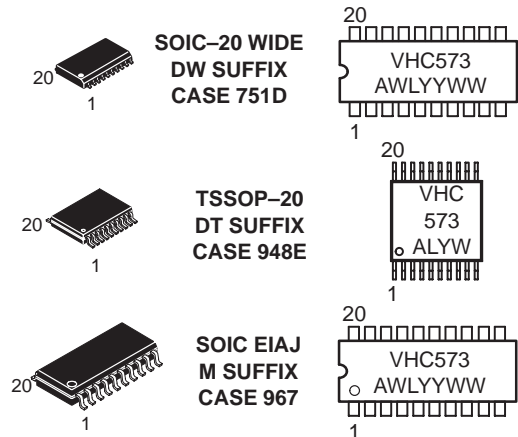
INPUTS			OUTPUT
$\overline{\text{OE}}$	LE	D	Q
L	H	H	H
L	H	L	L
L	L	X	No Change
H	X	X	Z



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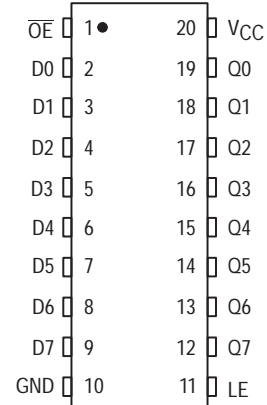
<http://onsemi.com>

MARKING DIAGRAMS



A = Assembly Location
 WL = Wafer Lot
 YY = Year
 WW = Work Week

PIN ASSIGNMENT



ORDERING INFORMATION

Device	Package	Shipping
MC74VHC573DW	SOIC-WIDE	38 / Rail
MC74VHC573DWR2	SOIC-WIDE	1000 / Reel
MC74VHC573DT	TSSOP-20	75 / Rail
MC74VHC573DTR2	TSSOP-20	2500 / Reel
MC74VHC573M	SOIC EIAJ	40 / Rail
MC74VHC573MEL	SOIC EIAJ	2000 / Reel

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MAXIMUM RATINGS*

Symbol	Parameter	Value	Unit
V _{CC}	DC Supply Voltage	- 0.5 to + 7.0	V
V _{in}	DC Input Voltage	- 0.5 to + 7.0	V
V _{out}	DC Output Voltage	- 0.5 to V _{CC} + 0.5	V
I _{IK}	Input Diode Current	- 20	mA
I _{OK}	Output Diode Current	± 20	mA
I _{out}	DC Output Current, per Pin	± 25	mA
I _{CC}	DC Supply Current, V _{CC} and GND Pins	± 75	mA
P _D	Power Dissipation in Still Air, SOIC Packages† TSSOP Package†	500 450	mW
T _{stg}	Storage Temperature	- 65 to + 150	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND ≤ (V_{in} or V_{out}) ≤ V_{CC}. Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

* Absolute maximum continuous ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute-maximum-rated conditions is not implied.

† Derating — SOIC Packages: - 7 mW/°C from 65° to 125°C
TSSOP Package: - 6.1 mW/°C from 65° to 125°C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V _{CC}	DC Supply Voltage	2.0	5.5	V
V _{in}	DC Input Voltage	0	5.5	V
V _{out}	DC Output Voltage	0	V _{CC}	V
T _A	Operating Temperature	- 40	+ 85	°C
t _r , t _f	Input Rise and Fall Time	V _{CC} = 3.3V V _{CC} = 5.0V	0 100 20	ns/V

DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test Conditions	V _{CC} V	T _A = 25°C			T _A = - 40 to 85°C		Unit
				Min	Typ	Max	Min	Max	
V _{IH}	Minimum High-Level Input Voltage		2.0 3.0 to 5.5	1.50 V _{CC} x 0.7			1.50 V _{CC} x 0.7		V
V _{IL}	Maximum Low-Level Input Voltage		2.0 3.0 to 5.5			0.50 V _{CC} x 0.3		0.50 V _{CC} x 0.3	V
V _{OH}	Minimum High-Level Output Voltage	V _{in} = V _{IH} or V _{IL} I _{OH} = - 50µA	2.0 3.0 4.5	1.9 2.9 4.4	2.0 3.0 4.5		1.9 2.9 4.4		V
		V _{in} = V _{IH} or V _{IL} I _{OH} = - 4mA I _{OH} = - 8mA	3.0 4.5	2.58 3.94			2.48 3.80		
V _{OL}	Maximum Low-Level Output Voltage	V _{in} = V _{IH} or V _{IL} I _{OL} = 50µA	2.0 3.0 4.5		0.0 0.0 0.0	0.1 0.1 0.1		0.1 0.1 0.1	V
		V _{in} = V _{IH} or V _{IL} I _{OL} = 4mA I _{OL} = 8mA	3.0 4.5			0.36 0.36		0.44 0.44	
I _{in}	Maximum Input Leakage Current	V _{in} = 5.5 V or GND	0 to 5.5			± 0.1		± 1.0	µA

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DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test Conditions	V _{CC} V	T _A = 25°C			T _A = -40 to 85°C		Unit
				Min	Typ	Max	Min	Max	
I _{OZ}	Maximum Three-State Leakage Current	V _{in} = V _{IL} or V _{IH} V _{out} = V _{CC} or GND	5.5			± 0.25		± 2.5	μA
I _{CC}	Maximum Quiescent Supply Current	V _{in} = V _{CC} or GND	5.5			4.0		40.0	μA

AC ELECTRICAL CHARACTERISTICS (Input t_r = t_f = 3.0ns)

Symbol	Parameter	Test Conditions	T _A = 25°C			T _A = -40 to 85°C		Unit
			Min	Typ	Max	Min	Max	
t _{PLH} , t _{PHL}	Maximum Propagation Delay, LE to Q	V _{CC} = 3.3 ± 0.3V C _L = 15pF		7.6	11.9	1.0	14.0	ns
		V _{CC} = 3.3 ± 0.3V C _L = 50pF		10.1	15.4	1.0	17.5	
t _{PLH} , t _{PHL}	Maximum Propagation Delay, LE to Q	V _{CC} = 5.0 ± 0.5V C _L = 15pF		5.0	7.7	1.0	9.0	ns
		V _{CC} = 5.0 ± 0.5V C _L = 50pF		6.5	9.7	1.0	11.0	
t _{PLH} , t _{PHL}	Maximum Propagation Delay, D to Q	V _{CC} = 3.3 ± 0.3V C _L = 15pF		7.0	11.0	1.0	13.0	ns
		V _{CC} = 3.3 ± 0.3V C _L = 50pF		9.5	14.5	1.0	16.5	
t _{PZH} , t _{ZLH}	Output Enable Time, OE to Q	V _{CC} = 3.3 ± 0.3V C _L = 15pF		7.3	11.5	1.0	13.5	ns
		V _{CC} = 3.3 ± 0.3V R _L = 1kΩ C _L = 50pF		9.8	15.0	1.0	17.0	
t _{PZH} , t _{ZLH}	Output Enable Time, OE to Q	V _{CC} = 5.0 ± 0.5V C _L = 15pF		5.2	7.7	1.0	9.0	ns
		V _{CC} = 5.0 ± 0.5V R _L = 1kΩ C _L = 50pF		6.7	9.7	1.0	11.0	
t _{PLZ} , t _{PHZ}	Output Disable Time, OE to Q	V _{CC} = 3.3 ± 0.3V C _L = 50pF		10.7	14.5	1.0	16.5	ns
		V _{CC} = 3.3 ± 0.3V R _L = 1kΩ C _L = 50pF						
t _{OSLH} , t _{OSHL}	Output to Output Skew	V _{CC} = 3.3 ± 0.3V C _L = 50pF (Note 1.)			1.5		1.5	ns
		V _{CC} = 5.5 ± 0.5V C _L = 50pF (Note 1.)			1.0		1.0	ns
C _{in}	Maximum Input Capacitance			4	10		10	pF
C _{out}	Maximum Three-State Output Capacitance (Output in High-Impedance State)			6				pF

C _{PD}	Power Dissipation Capacitance (Note 2.)	Typical @ 25°C, V _{CC} = 5.0V		pF
		Min	Max	
			29	

- Parameter guaranteed by design. t_{OSLH} = |t_{PLHm} - t_{PLHn}|, t_{OSHL} = |t_{PHLm} - t_{PHLn}|.
- C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}/8 (per latch). C_{PD} is used to determine the no-load dynamic power consumption; P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.

NOISE CHARACTERISTICS (Input t_r = t_f = 3.0ns, C_L = 50 pF, V_{CC} = 5.0V)

Symbol	Parameter	T _A = 25°C		Unit
		Typ	Max	
V _{OLP}	Quiet Output Maximum Dynamic V _{OL}	0.9	1.2	V
V _{OLV}	Quiet Output Minimum Dynamic V _{OL}	-0.9	-1.2	V
V _{IHD}	Minimum High Level Dynamic Input Voltage		3.5	V
V _{I LD}	Maximum Low Level Dynamic Input Voltage		1.5	V

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TIMING REQUIREMENTS (Input $t_r = t_f = 3.0\text{ns}$)

Symbol	Parameter	Test Conditions	$T_A = 25^\circ\text{C}$		$T_A = -40$ to 85°C	Unit
			Typ	Limit	Limit	
$t_{w(h)}$	Minimum Pulse Width, LE	$V_{CC} = 3.3 \pm 0.3\text{V}$ $V_{CC} = 5.0 \pm 0.5\text{V}$		5.0 5.0	5.0 5.0	ns
t_{su}	Minimum Setup Time, D to LE	$V_{CC} = 3.3 \pm 0.3\text{V}$ $V_{CC} = 5.0 \pm 0.5\text{V}$		3.5 3.5	3.5 3.5	ns
t_h	Minimum Hold Time, D to LE	$V_{CC} = 3.3 \pm 0.3\text{V}$ $V_{CC} = 5.0 \pm 0.5\text{V}$		1.5 1.5	1.5 1.5	ns

SWITCHING WAVEFORMS

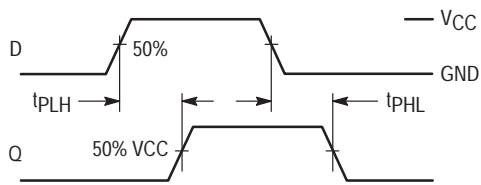


Figure 1.

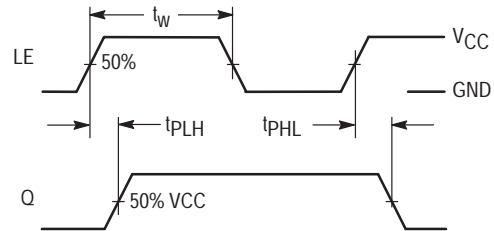


Figure 2.

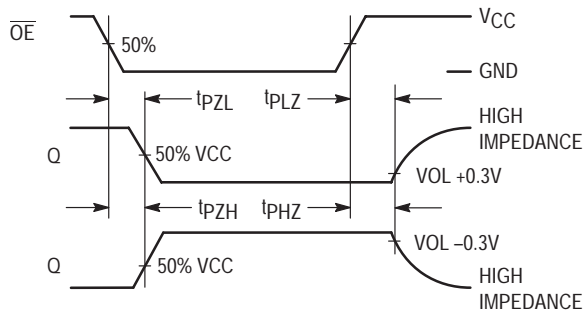


Figure 3.

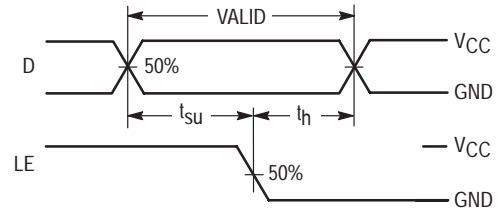
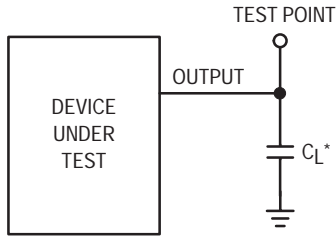


Figure 4.

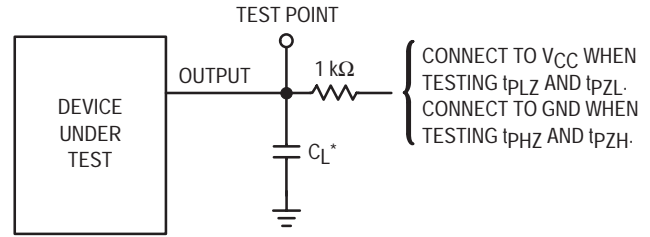
MC74VHC573

TEST CIRCUITS



*Includes all probe and jig capacitance

Figure 5.



*Includes all probe and jig capacitance

Figure 6.

EXPANDED LOGIC DIAGRAM

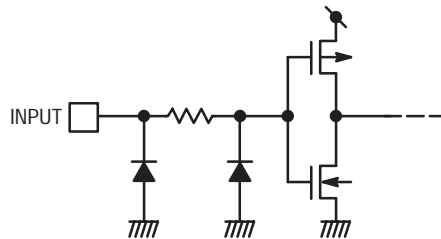
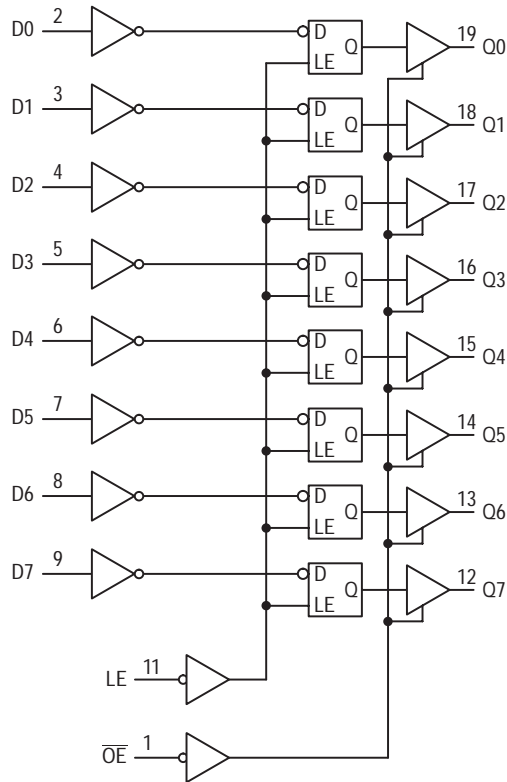
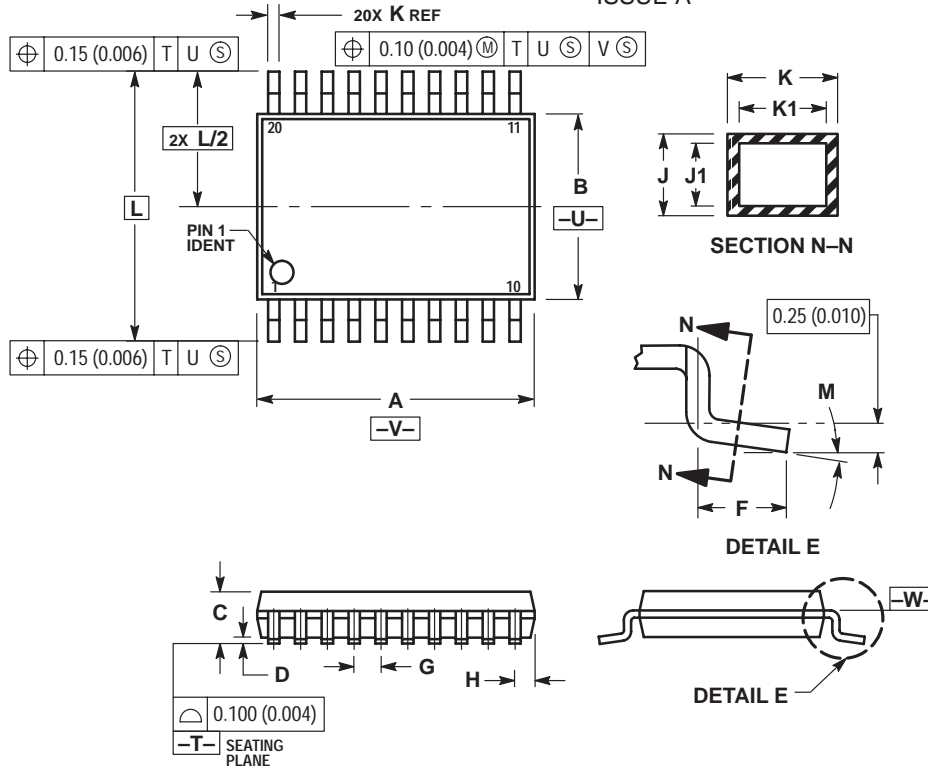


Figure 7. Input Equivalent Circuit

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PACKAGE DIMENSIONS

TSSOP-20
DT SUFFIX
CASE 948E-02
ISSUE A

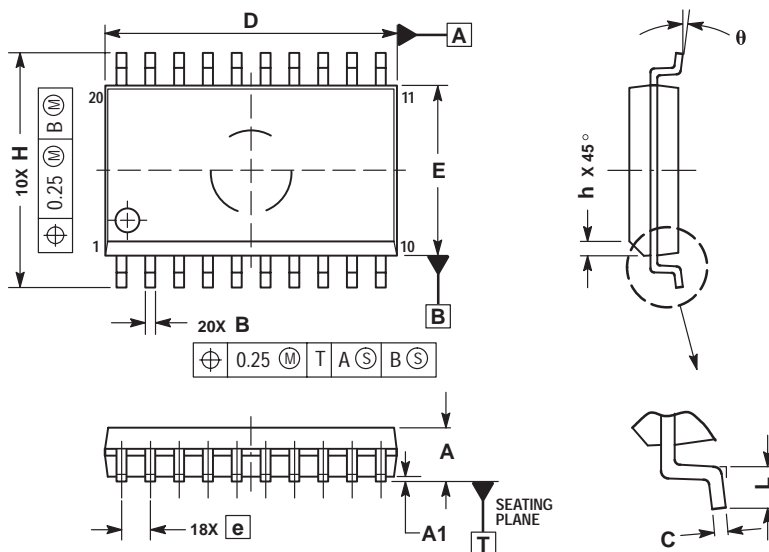


NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: MILLIMETER.
- DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
- DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
- DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
- TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
- DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	6.40	6.60	0.252	0.260
B	4.30	4.50	0.169	0.177
C	---	1.20	---	0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
H	0.27	0.37	0.011	0.015
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0°	8°	0°	8°

SO-20
DW SUFFIX
CASE 751D-05
ISSUE F



NOTES:

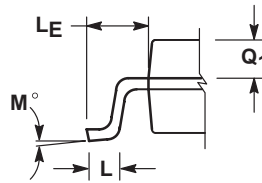
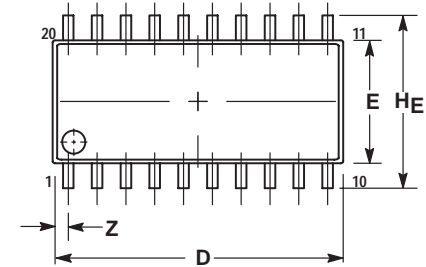
- DIMENSIONS ARE IN MILLIMETERS.
- INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSION.
- MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
- DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL CONDITION.

DIM	MIN	MAX
A	2.35	2.65
A1	0.10	0.25
B	0.35	0.49
C	0.23	0.32
D	12.65	12.95
E	7.40	7.60
e	1.27 BSC	
H	10.05	10.55
h	0.25	0.75
L	0.50	0.90
theta	0°	7°

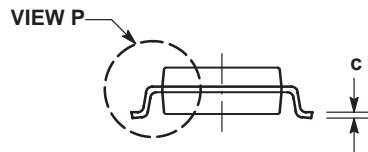
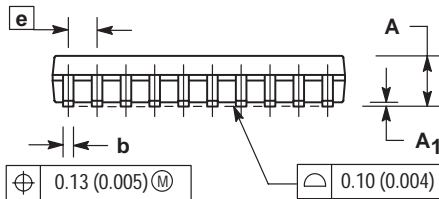
MC74VHC573

PACKAGE DIMENSIONS

SOIC EIAJ
M SUFFIX
CASE 967-01
ISSUE O



DETAIL P



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
5. THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	---	2.05	---	0.081
A1	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
c	0.18	0.27	0.007	0.011
D	12.35	12.80	0.486	0.504
E	5.10	5.45	0.201	0.215
e	1.27 BSC		0.050 BSC	
HE	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
LE	1.10	1.50	0.043	0.059
M	0°	10°	0°	10°
Q1	0.70	0.90	0.028	0.035
Z	---	0.81	---	0.032

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